# Dual High-Voltage Trench MOS Barrier Schottky Rectifier <br> Ultra Low $\mathrm{V}_{\mathrm{F}}=0.50 \mathrm{~V}$ at $\mathrm{I}_{\mathrm{F}}=5 \mathrm{~A}$ 



TO-263AB


VB20100C


ITO-220AB


VF20100C


TO-262AA


VI20100C


| PRIMARY CHARACTERISTICS |  |
| :---: | :---: |
| $\mathrm{I}_{\mathrm{F}(\mathrm{AV})}$ | $2 \times 10 \mathrm{~A}$ |
| $\mathrm{~V}_{\mathrm{RRM}}$ | 100 V |
| $\mathrm{I}_{\mathrm{FSM}}$ | 150 A |
| $\mathrm{~V}_{\mathrm{F}}$ at $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~A}$ | 0.58 V |
| $\mathrm{~T}_{J} \max$. | $150^{\circ} \mathrm{C}$ |

## FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of $245^{\circ} \mathrm{C}$ (for TO-263AB package)
- Solder bath temperature $275{ }^{\circ} \mathrm{C}$ maximum, 10 s , per JESD 22-B106 (for TO-220AB, ITO-220AB and TO-262AA package)
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC


## TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

## MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB and TO-262AA
Molding compound meets UL 94 V-0 flammability rating
Base P/N-E3 - RoHS compliant, commercial grade
Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102
E3 suffix meets JESD 201 class 1A whisker test
Polarity: As marked
Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS $\left(T_{A}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| PARAMETER | SYMBOL | V20100C | VF20100C | VB20100C | VI20100C | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Maximum repetitive peak reverse voltage | $V_{\text {RRM }}$ | 100 |  |  |  | V |
| Maximum average forward rectified current (fig. 1) $\begin{aligned} & \text { per device } \\ & \text { per diode }\end{aligned}$ | $\mathrm{I}_{\mathrm{F}(\mathrm{AV})}$ | $\begin{aligned} & 20 \\ & 10 \end{aligned}$ |  |  |  | A |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode | $\mathrm{I}_{\text {FSM }}$ | 150 |  |  |  | A |
| Non-repetitive avalanche energy at $\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}, \mathrm{L}=60 \mathrm{mH}$ per diode | $\mathrm{E}_{\text {AS }}$ | 150 |  |  |  | mJ |
| Peak repetitive reverse current at $\mathrm{t}_{\mathrm{p}}=2 \mu \mathrm{~s}, 1 \mathrm{kHz}$, $\mathrm{T}_{\mathrm{J}}=38^{\circ} \mathrm{C} \pm 2^{\circ} \mathrm{C}$ per diode | $\mathrm{I}_{\text {RRM }}$ | 1.0 |  |  |  | A |
| Voltage rate of change (rated $\mathrm{V}_{\mathrm{R}}$ ) | $\mathrm{dV} / \mathrm{dt}$ | 10000 |  |  |  | $\mathrm{V} / \mu \mathrm{s}$ |
| Isolation voltage (ITO-220AB only) from terminal to heatsink $t=1 \mathrm{~min}$ | $\mathrm{V}_{\mathrm{AC}}$ | 1500 |  |  |  | V |
| Operating junction and storage temperature range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {STG }}$ | -40 to +150 |  |  |  | ${ }^{\circ} \mathrm{C}$ |

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| PARAMETER | TEST CONDITIONS |  | SYMBOL | TYP. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Breakdown voltage per diode | $\mathrm{I}_{\mathrm{R}}=10 \mathrm{~mA}$ | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{V}_{\mathrm{BR}}$ | 105 (minimum) | - | V |
| Instantaneous forward voltage per diode ${ }^{(1)}$ | $\begin{aligned} & I_{F}=5 \mathrm{~A} \\ & \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} \end{aligned}$ | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $V_{F}$ | $\begin{aligned} & 0.55 \\ & 0.65 \end{aligned}$ | $0.79$ | V |
|  | $\begin{aligned} & I_{F}=5 \mathrm{~A} \\ & \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} \end{aligned}$ | $\mathrm{T}_{\mathrm{A}}=125^{\circ} \mathrm{C}$ |  | $\begin{aligned} & 0.50 \\ & 0.58 \end{aligned}$ | $0.68$ |  |
| Reverse current per diode ${ }^{(2)}$ | $\mathrm{V}_{\mathrm{R}}=70 \mathrm{~V}$ | $\begin{aligned} & \mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C} \\ & \mathrm{~T}_{\mathrm{A}}=125^{\circ} \mathrm{C} \end{aligned}$ | $I_{\text {R }}$ | $\begin{aligned} & 17 \\ & 5.3 \end{aligned}$ | - | $\mu \mathrm{A}$ <br> mA |
|  | $\mathrm{V}_{\mathrm{R}}=100 \mathrm{~V}$ | $\begin{aligned} & \mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C} \\ & \mathrm{~T}_{\mathrm{A}}=125^{\circ} \mathrm{C} \end{aligned}$ |  | $12$ | $\begin{gathered} 800 \\ 25 \end{gathered}$ | $\begin{aligned} & \mu \mathrm{A} \\ & \mathrm{~mA} \end{aligned}$ |

## Notes

${ }^{(1)}$ Pulse test: $300 \mu \mathrm{~s}$ pulse width, $1 \%$ duty cycle
${ }^{(2)}$ Pulse test: Pulse width $\leq 40 \mathrm{~ms}$

| THERMAL CHARACTERISTICS $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted) |  |  |  |  |  |  |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: |
| PARAMETER | SYMBOL | V20100C | VF20100C | VB20100C | VI20100C | UNIT |
| Typical thermal resistance per diode | $\mathrm{R}_{\text {өJC }}$ | 2.8 | 5.5 | 2.8 | 2.8 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |


| ORDERING INFORMATION (Example) |  |  |  |  |  |  |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: |
| PACKAGE | PREFERRED P/N | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |  |
| TO-220AB | V20100C-E3/4W | 1.881 | 4 W | $50 /$ tube | Tube |  |
| ITO-220AB | VF20100C-E3/4W | 1.75 | 4 W | $50 /$ tube | Tube |  |
| TO-263AB | VB20100C-E3/4W | 1.39 | 4 W | $50 /$ tube | Tube |  |
| TO-263AB | VB20100C-E3/8W | 1.39 | 8 W | $800 /$ reel | Tape and reel |  |
| TO-262AA | VI20100C-E3/4W | 1.452 | 4 W | $50 /$ tube | Tube |  |

## RATINGS AND CHARACTERISTICS CURVES

( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)


Figure 1. Maximum Forward Current Derating Curve


Figure 2. Forward Power Loss Characteristics Per Diode

V20100C, VF20100C, VB20100C \& VI20100C


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

Figure 4. Typical Reverse Characteristics Per Diode


Figure 6. Typical Transient Thermal Impedance Per Diode


Figure 7. Typical Transient Thermal Impedance Per Diode


Figure 5. Typical Junction Capacitance Per Diode

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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)


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